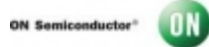
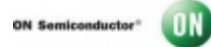


specificazioni	
Modello di prodotti	FDMS8660AS
fabbricante	Fairchild/ON Semiconductor
Descrizione	MOSFET N-CH 30V 28A POWER56
Categoria	Prodotti a semiconduttore discreti > Transistor-FET,
Stato parte	16479 pcs Stock
Vgs (th) (max) a Id	3V @ 1mA
Tecnologia	MOSFET (Metal Oxide)
Contenitore dispositivo fornitore	8-PQFN (5x6), Power56
Serie	PowerTrench®
Rds On (max) a Id, Vgs	2.1 mOhm @ 28A, 10V
Dissipazione di potenza (max)	2.5W (Ta), 104W (Tc)
imballaggio	Tape & Reel (TR)
Contenitore / involucro	8-PowerTDFN
temperatura di esercizio	-55°C ~ 150°C (TJ)
Tipo montaggio	Surface Mount
Capacità di ingresso (Ciss) (Max) @ Vds	5865pF @ 15V
Carica Gate (Qg) (Max) @ Vgs	83nC @ 10V
Tipo FET	N-Channel
Caratteristica FET	-
Tensione drain-source (Vdss)	30V
Corrente - Drain continuo (Id) @ 25 ° C	28A (Ta), 49A (Tc)

 FDMS8660S MOS FAIRCHILD FAIRCHILD QFN8	 FDMS86581_085 FAIRCHILD FDMS86581_085 FAIRCHILD	 FDMS8662 Fairchild/ON Semiconductor MOSFET N-CH 30V 28A POWER56	 FDMS8661AS FAIRCHILD FAIRCHILD PQOAM
 FDMS86580_F085 Fairchild/ON Semiconductor MOSFET N-CH 60V 50A POWER56	 FDMS86580-F085 AMI Semiconductor / ON Semiconductor MOSFET N-CH 60V 50A POWER56	 FDMS86581-F085 AMI Semiconductor / ON Semiconductor MOSFET N-CHANNEL 60V 30A 8PQFN	 FDMS8660S AMI Semiconductor / ON Semiconductor MOSFET N-CH 30V 25A POWER56

Di Più

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